

LDMOS, RF, 300W, UHF, 89V, Drain Source Voltage Vds:89V, Continuous Drain Current Id:7.6A, Power Dissipation Pd:300W, Operating Frequency Min:470MHz, Operating Frequency Max:860MHz

Manufacturers	NXP Semiconductor
Package/Case	SOT502B
Product Type	Transistors
RoHS	
Lifecycle	



Images are for reference only

Please submit RFQ for BLF878 or [Email to us: sales@ovaga.com](mailto:sales@ovaga.com) We will contact you in 12 hours.

[RFQ](#)

General Description

BLF878 is a high-power RF transistor designed for use in broadcast transmitters and other high-frequency applications. Here are some of its features:

Features

Frequency range: 470-860 MHz

Output power: 350 W

Efficiency: up to 50%

Input impedance: 50 ohms

Package: NI-1230S

Application

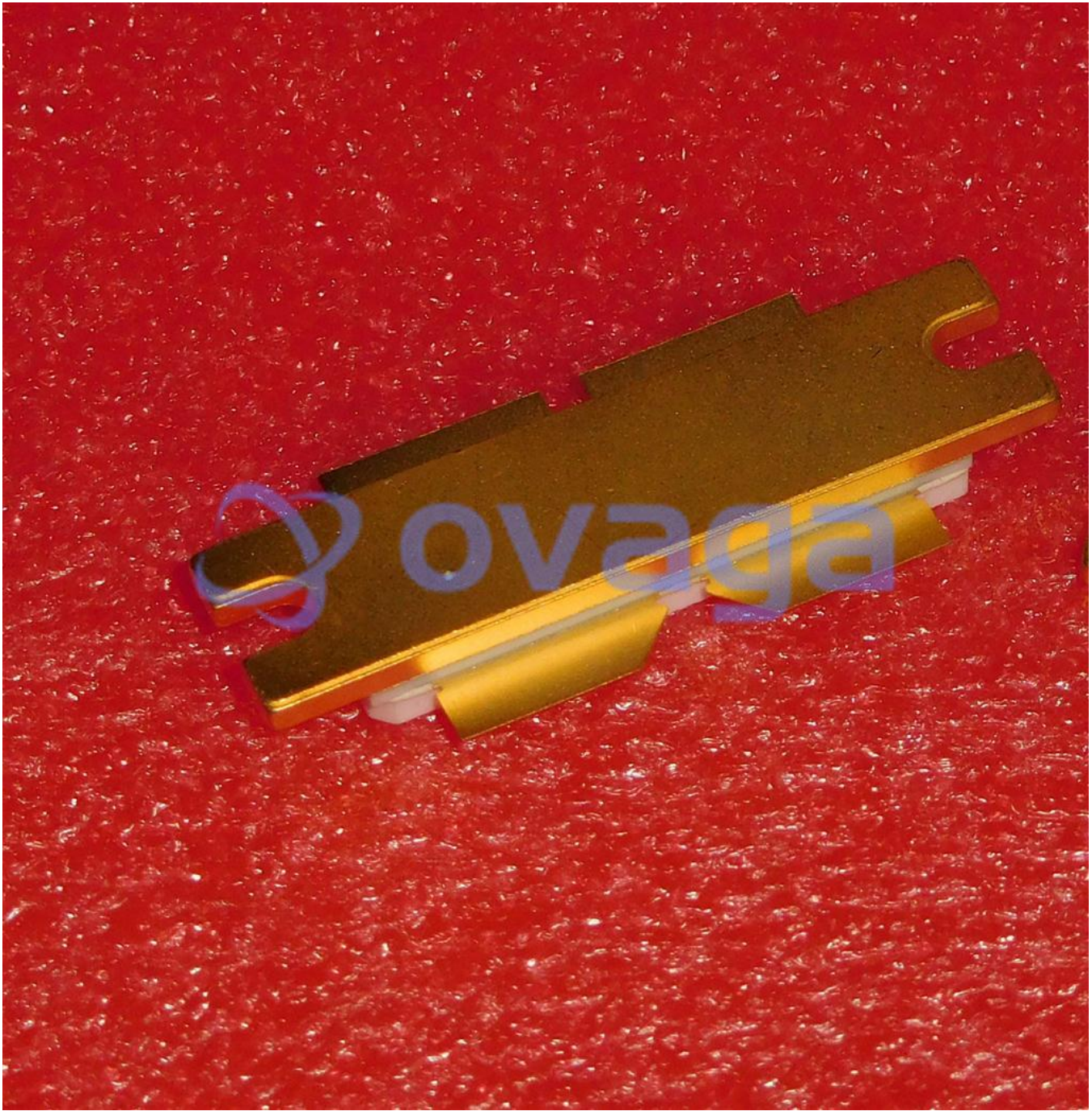
Broadcast transmitters for TV and radio

High-power amplifiers for wireless communication systems

Radar systems

Industrial heating equipment





Related Products



[BLT50](#)

NXP Semiconductor
SOT-223



[BLF871](#)

NXP Semiconductor
SOT467



[BLF574](#)

NXP Semiconductor
TO-59



[BLF278](#)

NXP Semiconductor
SOT-262



BLF245

NXP Semiconductor
SOT-123A



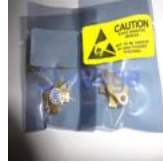
BLF642

NXP Semiconductor
SOT467C



BLF248

NXP Semiconductor
SOT-262 A1



BLF175

NXP Semiconductor
TO-59